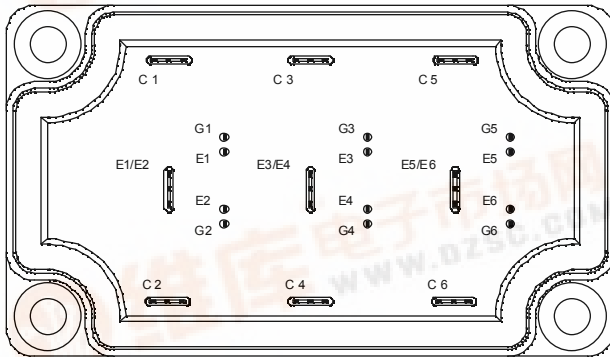
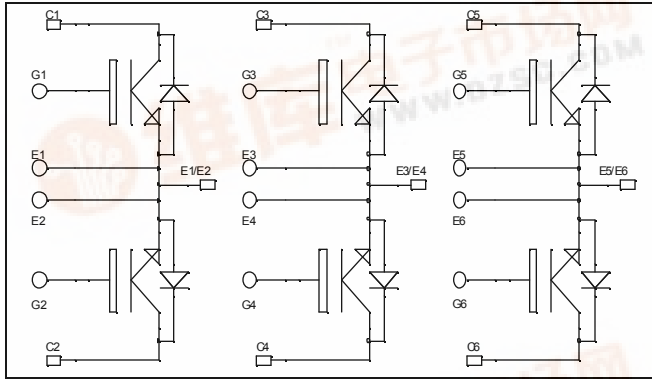




APTGF90TDU60PG

Triple dual Common Source NPT IGBT Power Module

$V_{CES} = 600V$
 $I_C = 90A @ T_c = 80^\circ C$



Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Non Punch Through (NPT) Fast IGBT®
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Easy paralleling due to positive TC of VCESat
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	315
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	416
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	200A @ 600V



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$			250	μA
		$V_{CE} = 600\text{V}$	$T_j = 125^\circ\text{C}$			500	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$	$T_j = 25^\circ\text{C}$		2.0	2.5	V
		$I_C = 90\text{A}$	$T_j = 125^\circ\text{C}$		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1\text{mA}$		3		5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$				± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$			4300		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$			470		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$			400		
Q_g	Total gate Charge	$V_{GE} = 15\text{V}$			330		nC
Q_{ge}	Gate – Emitter Charge	$V_{Bus} = 300\text{V}$			290		
Q_{gc}	Gate – Collector Charge	$I_C = 90\text{A}$			200		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			26		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$			25		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400\text{V}$			150		
T_f	Fall Time	$I_C = 90\text{A}$			30		
		$R_G = 5\ \Omega$					
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)			26		ns
T_r	Rise Time	$V_{GE} = 15\text{V}$			25		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400\text{V}$			170		
T_f	Fall Time	$I_C = 90\text{A}$			40		
		$R_G = 5\ \Omega$					
E_{on}	Turn-on Switching Energy	$V_{GE} = 15\text{V}$	$T_j = 125^\circ\text{C}$		4.3		mJ
		$V_{Bus} = 400\text{V}$					
E_{off}	Turn-off Switching Energy	$I_C = 90\text{A}$	$T_j = 125^\circ\text{C}$		3.5		
		$R_G = 5\ \Omega$					

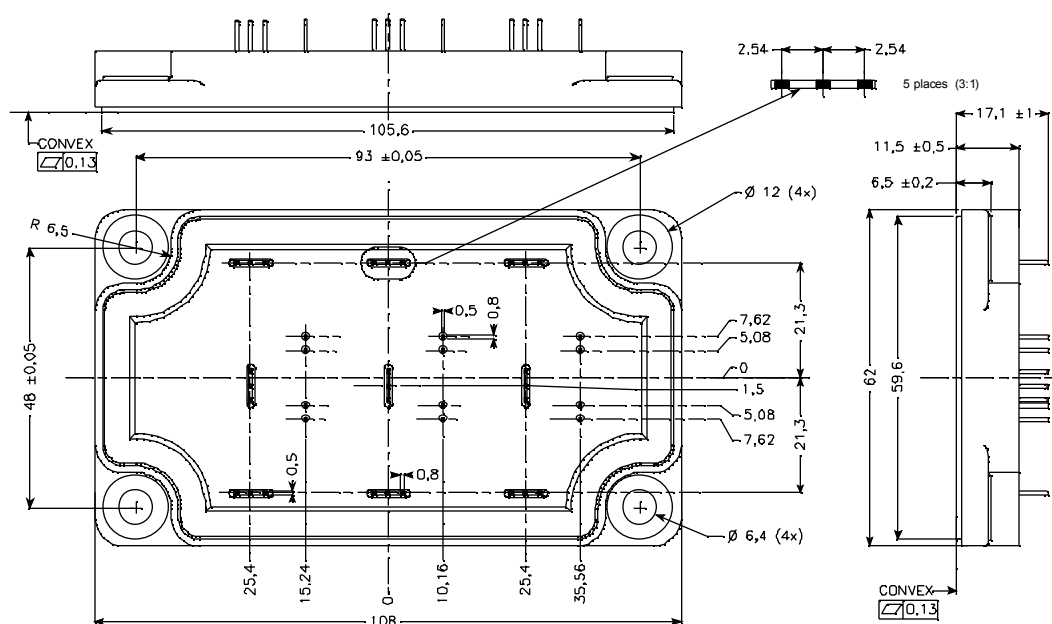
Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$			250	μA
			$T_j = 125^\circ\text{C}$			500	
I_F	DC Forward Current		$T_c = 70^\circ\text{C}$		60		A
V_F	Diode Forward Voltage	$I_F = 60\text{A}$			1.6	1.8	V
		$I_F = 120\text{A}$			1.9		
		$I_F = 60\text{A}$	$T_j = 125^\circ\text{C}$		1.4		
t_{rr}	Reverse Recovery Time	$I_F = 60\text{A}$	$T_j = 25^\circ\text{C}$		130		ns
		$V_R = 400\text{V}$	$T_j = 125^\circ\text{C}$		170		
Q_{rr}	Reverse Recovery Charge	$di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		220		nC
			$T_j = 125^\circ\text{C}$		920		

Thermal and package characteristics

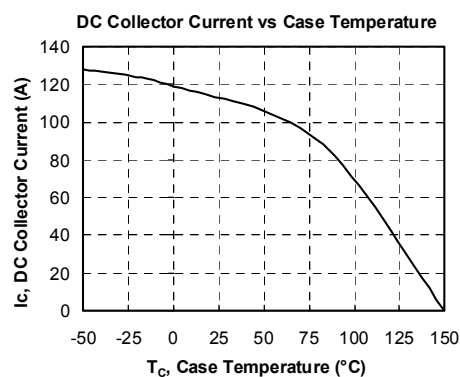
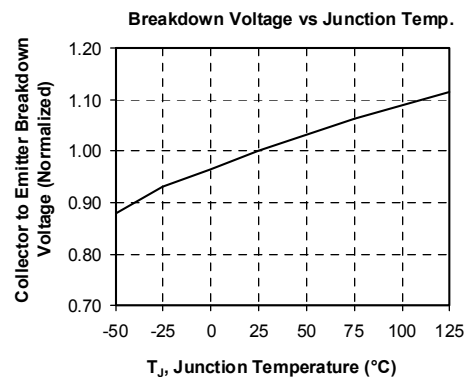
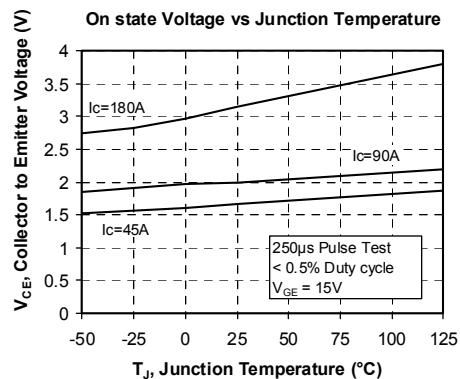
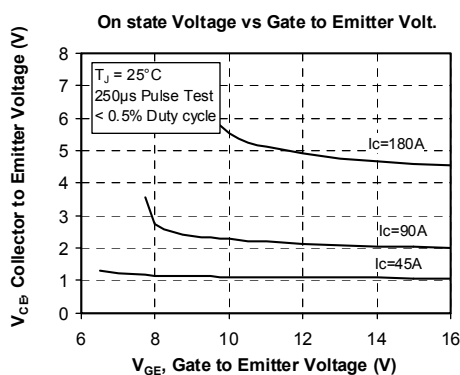
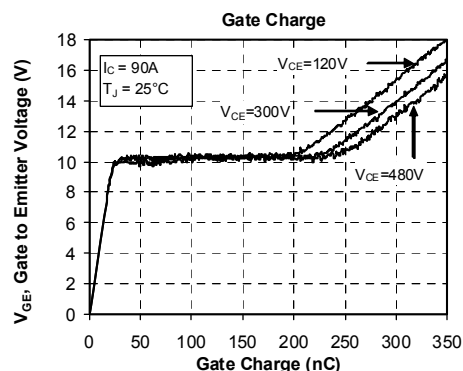
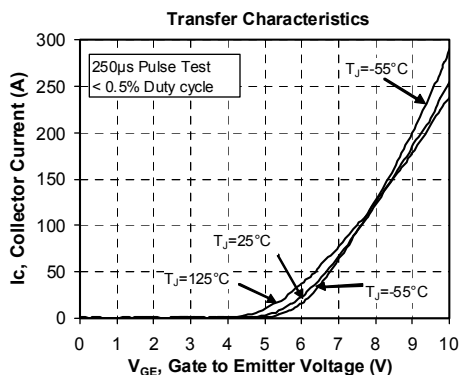
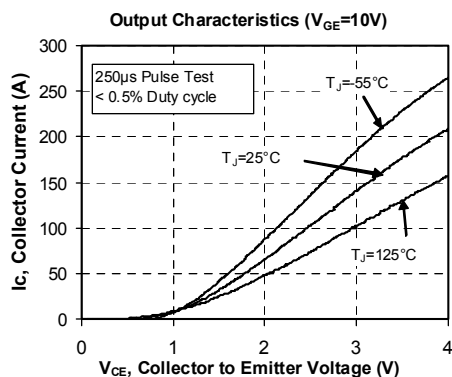
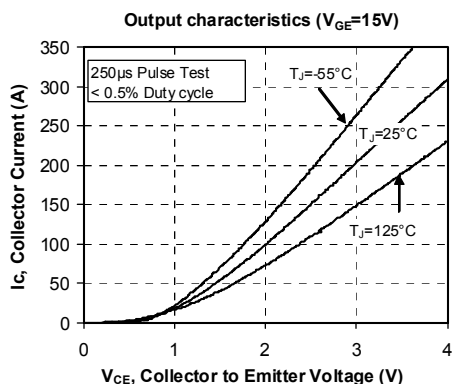
Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance			IGBT		0.3	°C/W
				Diode		0.9	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

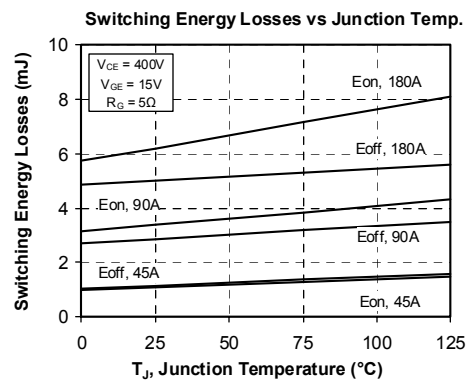
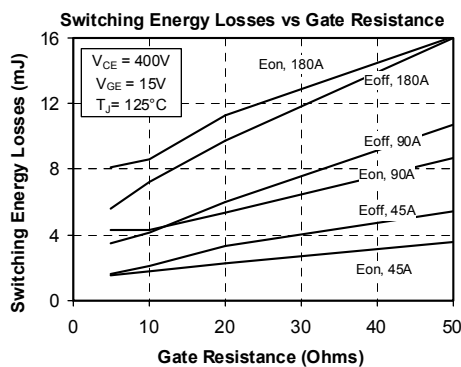
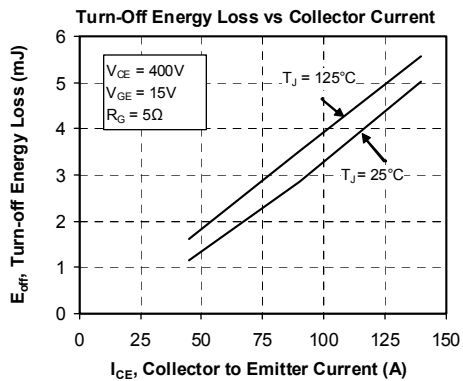
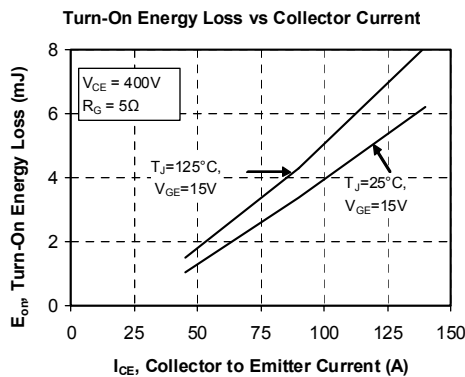
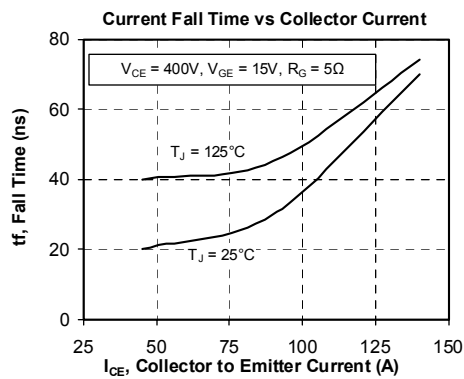
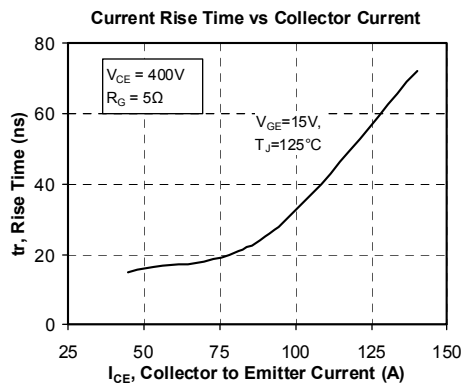
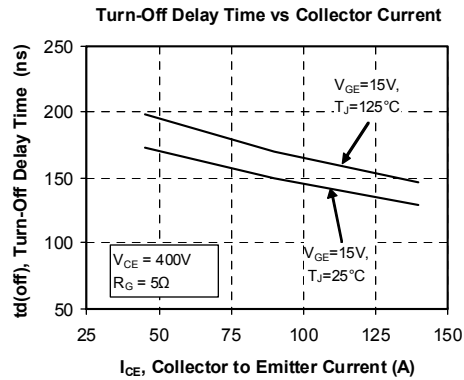
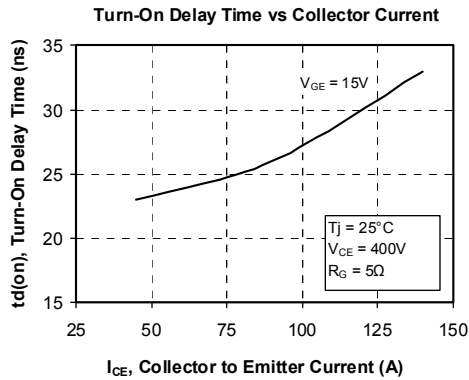
SP6-P Package outline (dimensions in mm)

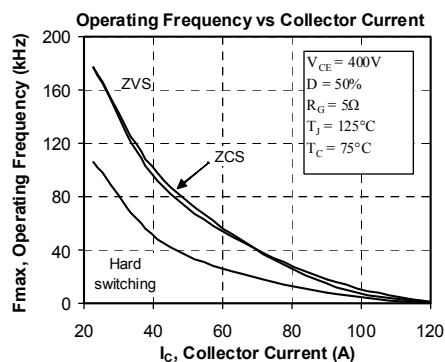
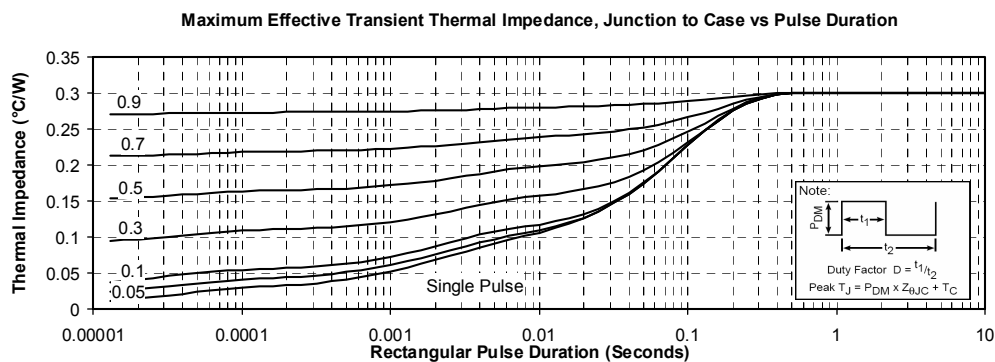
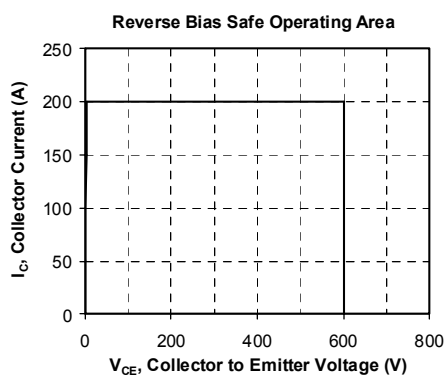
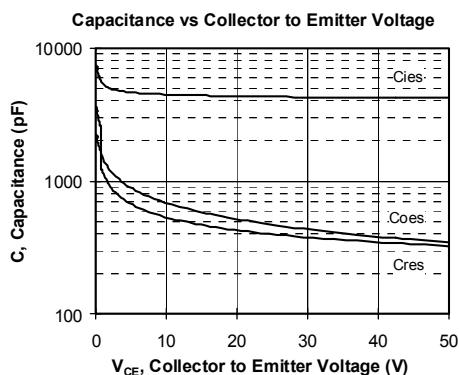


See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

Typical Performance Curve







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